



Docket No.: M4065.0319/P319-A  
(PATENT)

A20/F  
5/27/03  
John Th

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Ronald A. Weimer, et al.

Application No.: 09/912,558

Group Art Unit: 2813

Filed: July 26, 2001

Examiner: Erik J. Kielin

For: FABRICATION OF DRAM AND OTHER  
SEMICONDUCTOR DEVICES WITH AN  
INSULATING FILM USING A WET RAPID  
THERMAL OXIDATION PROCESS

RECEIVED  
MAY 22 2003  
TECHNOLOGY CENTER 2800

AMENDMENT

BOX: Non-Fee Amendment  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated February 24, 2003 rejecting claims 13, 14, 16, 17, and 41-43, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please rewrite claims 13 and 41-43 as follows:

13. (Four Times Amended) A method of fabricating a semiconductor device,  
the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to  
form part of a gate of a transistor; and